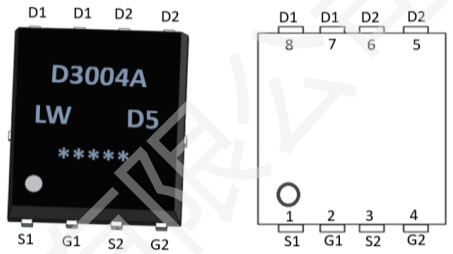
General Description:

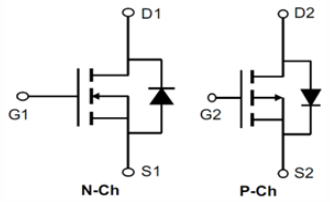
The LWD3004AD5 uses trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications. The package form is PDFN5*6-8L, which accords with the ROHS standard and Halogen Free standard.

Symbol	N-Ch	P-Ch	Units
V_{DSS}	30	-30	V
I_D	25	-20	A
$R_{DS(ON)\ TYPE}$	8.5	20.5	mΩ

Marking and Pin Assignment



Inner Equivalent Principium Chart



Features:

- Fast Switching
- Low Gate Charge and $R_{DS(ON)}$
- Low Reverse transfer capacitances

Applications:

- DC-DC Converter
- Portable Equipment
- Power Management

100% DVDS Tested

100% Avalanche Tested

RoHS HF

Package Marking and Ordering Information:

Marking	Part Number	Package	Packing	Qty.
D3004A/LW D5/D.C.	LWD3004AD5	PDFN5*6-8L	Reel	5000 Pcs

Absolute Maximum Ratings:

Symbol	Parameter		Value		Units
			N-Ch	P-Ch	
V_{DSS}	Drain-to-Source Voltage		30	-30	V
I_D	Continuous Drain Current	T_C=25℃	25	-20	A
	Continuous Drain Current	T_C=100℃	16	-13	A
I_{DM}[a1]	Pulsed Drain Current		100	-80	A
E_{AS}[a2]	Single pulse avalanche energy		39	34	mJ
V_{GS}	Gate-to-Source Voltage		±20	±20	V
P_D	Power Dissipation		21	21	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range		150, -55 to 150		℃
T_L	Maximum Temperature for Soldering		260		℃

Thermal Characteristics:

Symbol	Parameter	Value		Units
		N-Ch	P-Ch	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	6.0	6.0	℃/W
$R_{\theta JA}$[a3]	Thermal Resistance, Junction-to-Ambient	40	40	℃/W

N-Channel Electrical Characteristic (T_J = 25 °C, unless otherwise specified):

Static Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
V_{DSS}	Drain to Source Breakdown Voltage	V_{GS}=0V, I_D=250μA	30	--	--	V
I_{DSS}	Drain to Source Leakage Current	V_{DS}=30V, V_{GS}=0V	--	--	1.0	μA
$I_{GSS(F)}$	Gate to Source Forward Leakage	V_{GS}=+20V, V_{DS}=0V	--	--	100	nA
$I_{GSS(R)}$	Gate to Source Reverse Leakage	V_{GS}=-20V, V_{DS}=0V	--	--	-100	nA
$V_{GS(TH)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250μA	1.0	1.5	2.0	V
$R_{DS(ON)1}$	Drain-to-Source On-Resistance	V_{GS}=10V, I_D=15A	--	8.5	12	mΩ
$R_{DS(ON)2}$	Drain-to-Source On-Resistance	V_{GS}=4.5V, I_D=10A	--	12.5	20	mΩ

Dynamic Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
C_{iss}	Input Capacitance	V_{GS} =0V V_{DS} =15V f =1.0MHz	--	762	--	pF
C_{oss}	Output Capacitance		--	111	--	
C_{rss}	Reverse Transfer Capacitance		--	96	--	
R_G	Gate resistance	V_{GS}=0V,V_{DS}=0V,f=1MHz	--	2.0	--	Ω

Resistive Switching Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
$t_{d(ON)}$	Turn-on Delay Time	I_D =15A V_{DS} =15V V_{GS} =10V R_G =6.0Ω	--	11	--	ns
t_r	Rise Time		--	20	--	
$t_{d(OFF)}$	Turn-Off Delay Time		--	30	--	
t_f	Fall Time		--	10	--	
Q_g	Total Gate Charge	V_{GS} =10V V_{DS} =15V I_D =15A	--	17	--	nC
Q_{gs}	Gate to Source Charge		--	2.3	--	
Q_{gd}	Gate to Drain Charge		--	3.4	--	

Source-Drain Diode Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
I_S	Diode Forward Current	T_C=25 °C	--	--	25	A
V_{SD}	Diode Forward Voltage	I_S=15A, V_{GS}=0V	--	--	1.2	V

a1：Repetitive rating; pulse width limited by maximum junction temperature

a2：V_{DD}=15V, L=0.1mH, R_G=25Ω, Starting T_J=25 ℃

a3：Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm^2 (one layer, 70 μm thick) copper area for drain connection.

N-Channel Characteristics Curve：

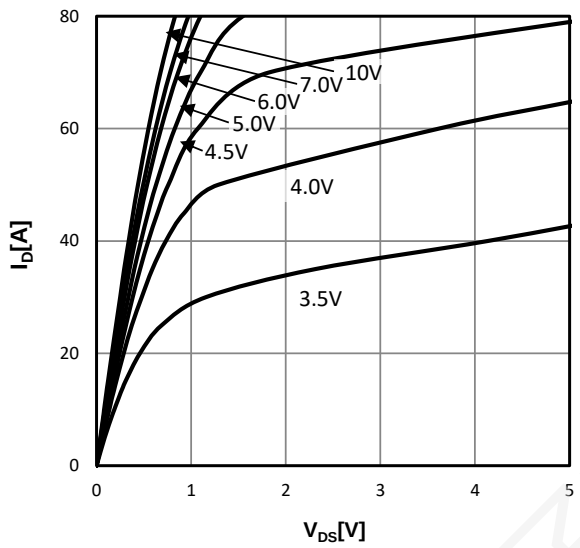
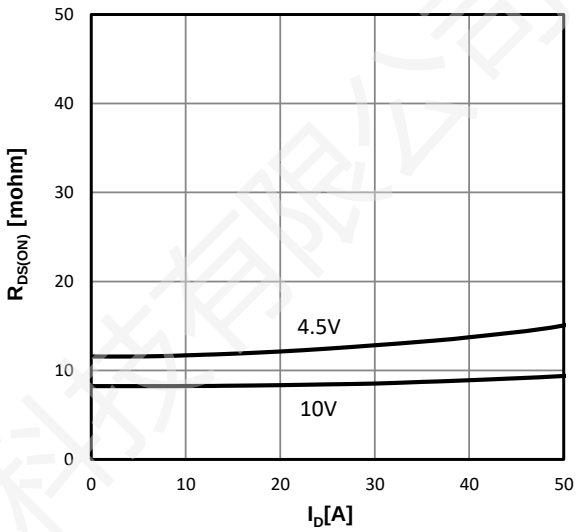
Figure 1: Typ. output characteristics	Figure 2: Typ. drain-source on resistance
	
$I_D=f(V_{DS})$, T_j=25 °C; parameter: V_{GS}	$R_{DS(on)}=f(I_D)$, T_j=25 °C; parameter: V_{GS}

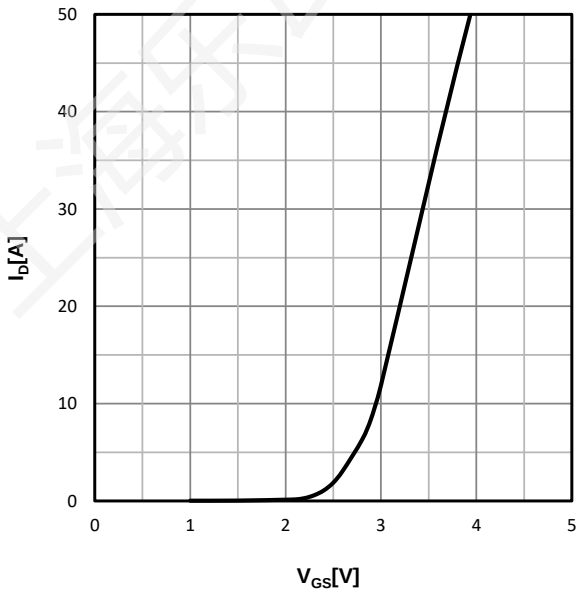
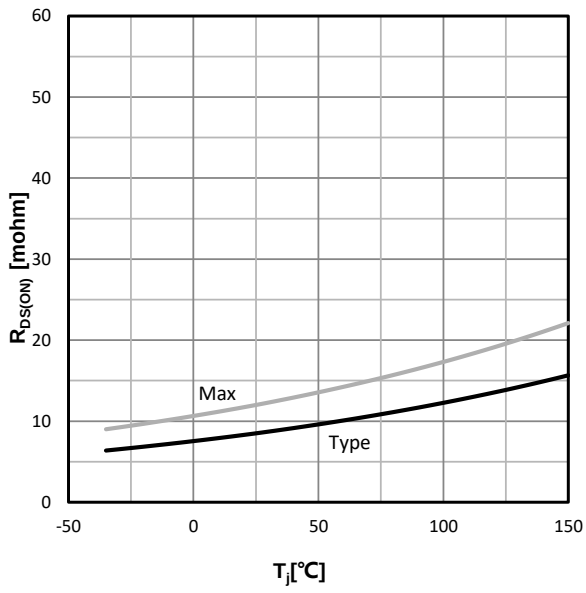
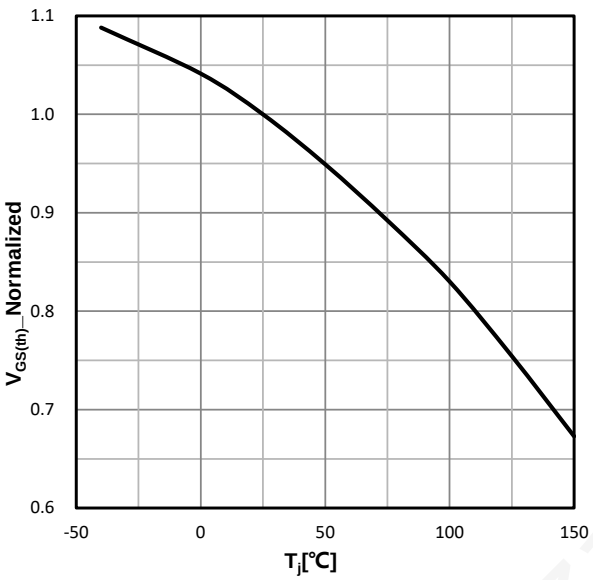
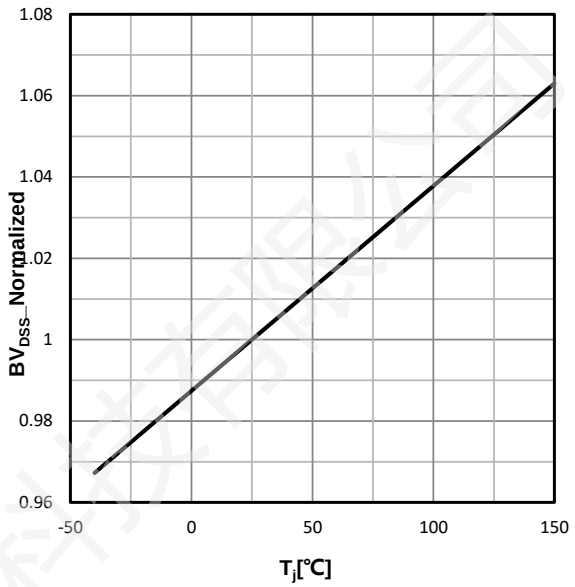
Figure 3: Typ. transfer characteristics	Figure 4: drain-source on resistance
	
$I_D=f(V_{GS})$, $\|V_{DS}\|>2\|I_D\|R_{DS}(on)max$;	$R_{DS(on)}=f(T_j)$, I_D=15A, V_{GS}=10V;

Figure 5: Typ. gate threshold voltage



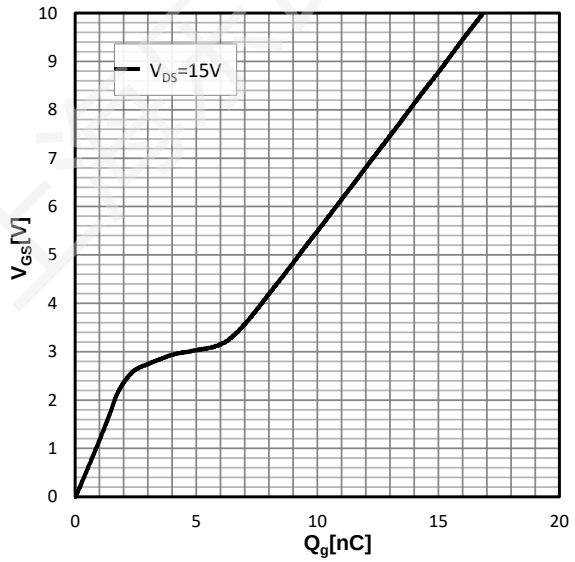
$V_{GS}=f(T_j)$,$V_{GS}=V_{DS,}I_D=250\mu A$;

Figure 6: Drain-source breakdown voltage



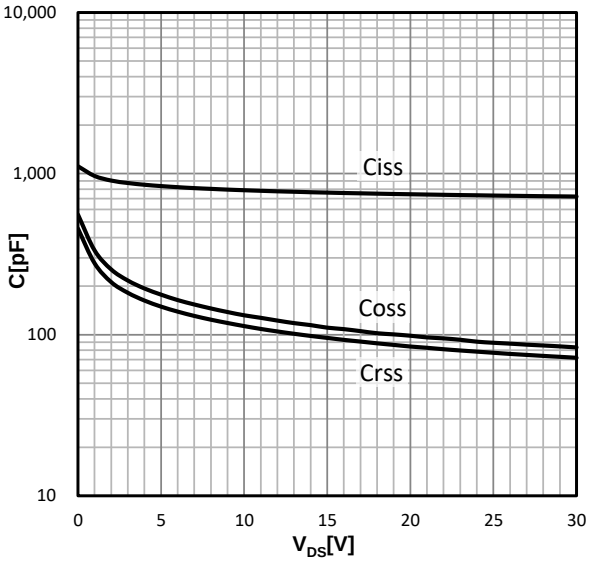
$V_{BR(DSS)}=f(T_j)$; $I_D=250\mu A$;

Figure 7: Typ. gate charge



$V_{GS}=f(Q_g)$, $I_D=15A$, $T_j=25$ °C; parameter: V_{DS}

Figure 8: Typ. Capacitances



$C=f(V_{DS})$; $V_{GS}=0V$; f=1.0 MHz;

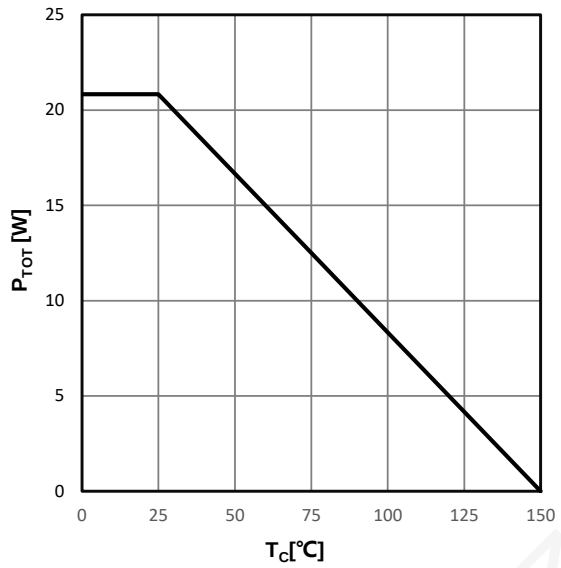
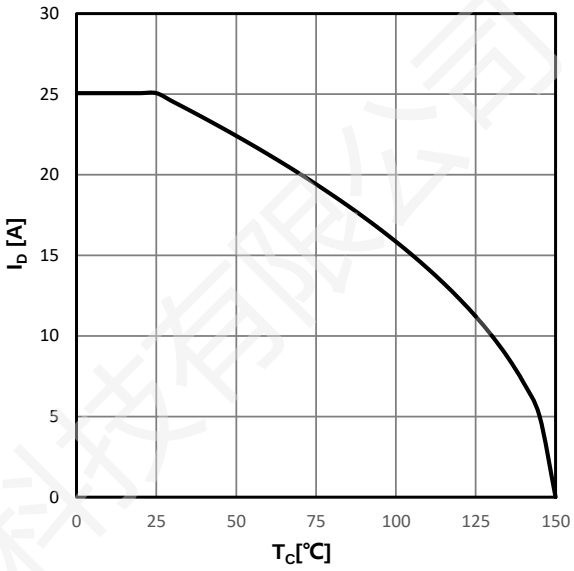
Figure 9: Power dissipation	Figure 10:Drain current
	
$P_{tot}=f(T_C)$;	$I_D=f(T_C)$;

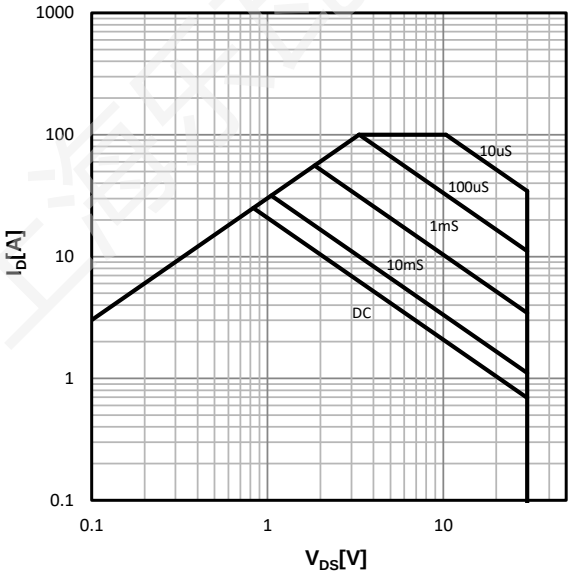
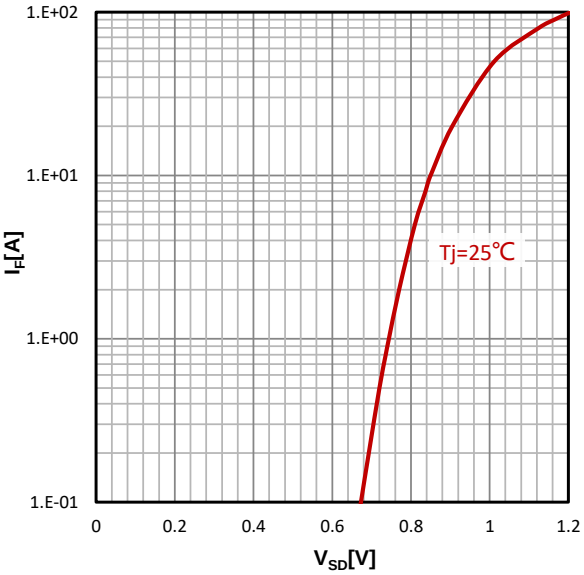
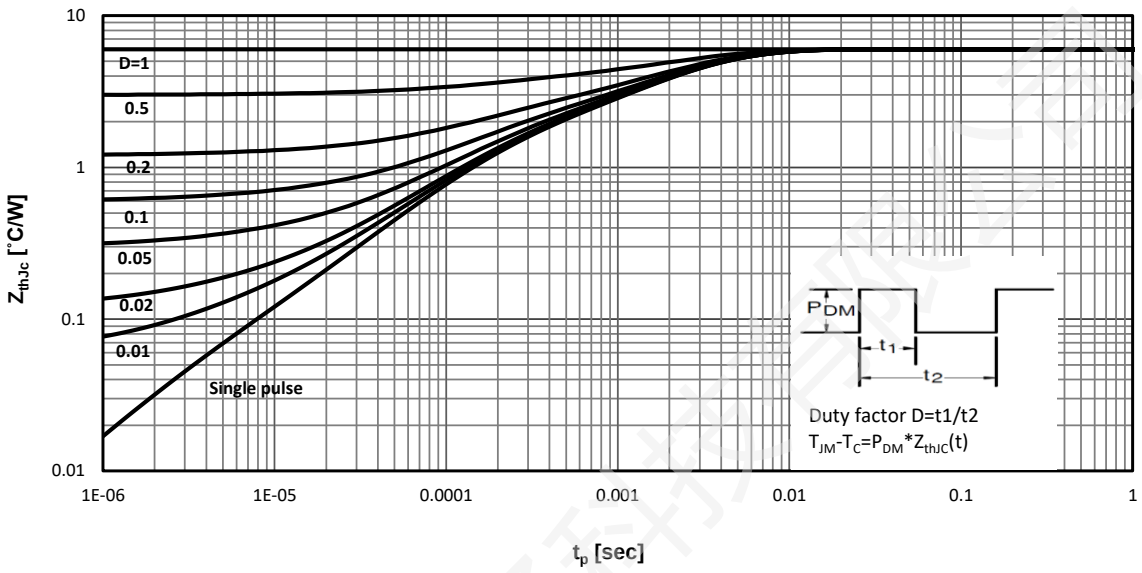
Figure 11: Safe operating area	Figure 12: Typ. forward characteristics
	
$I_D=f(V_{DS})$; T_C=25 °C; D=0; parameter: tp	$I_F=f(V_{SD})$;

Figure 13: Max. Transient Thermal Impedance



$Z_{thJC}=f(t_p)$; parameter: D

Test Circuit & Waveform:

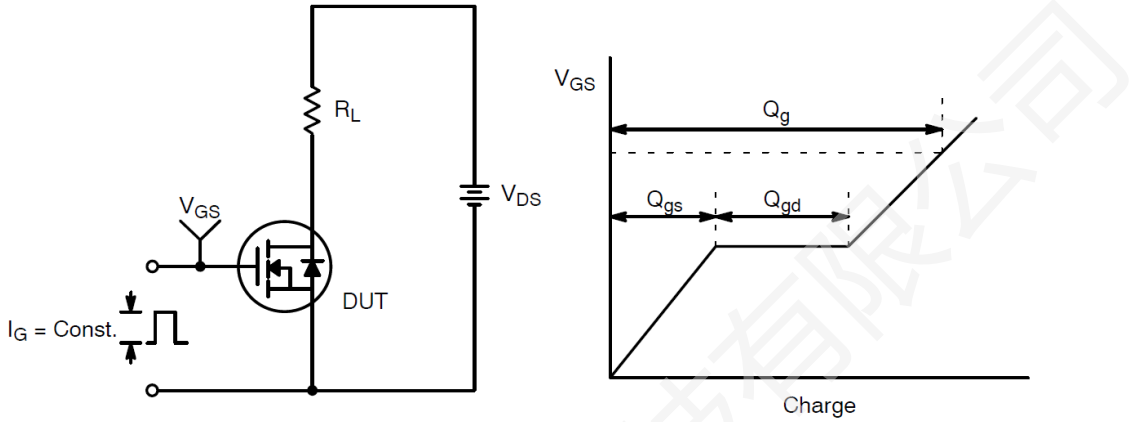


Figure 14: Gate Charge Test Circuit & Waveform

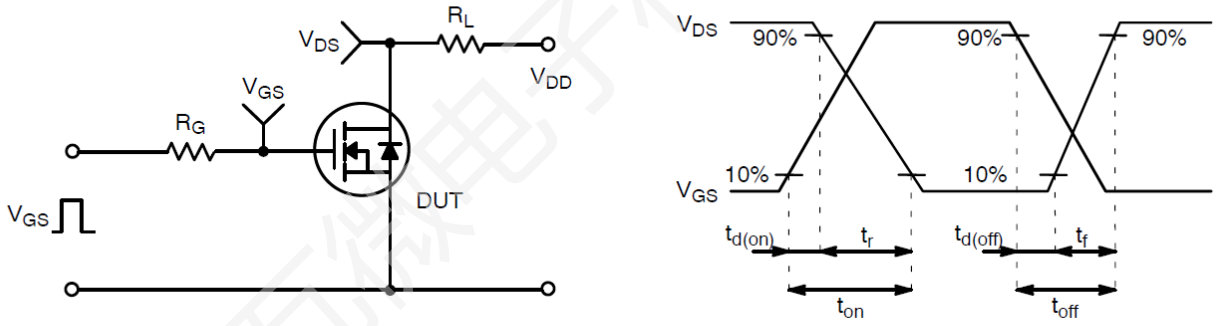


Figure 15: Resistive Switching Test Circuit & Waveforms

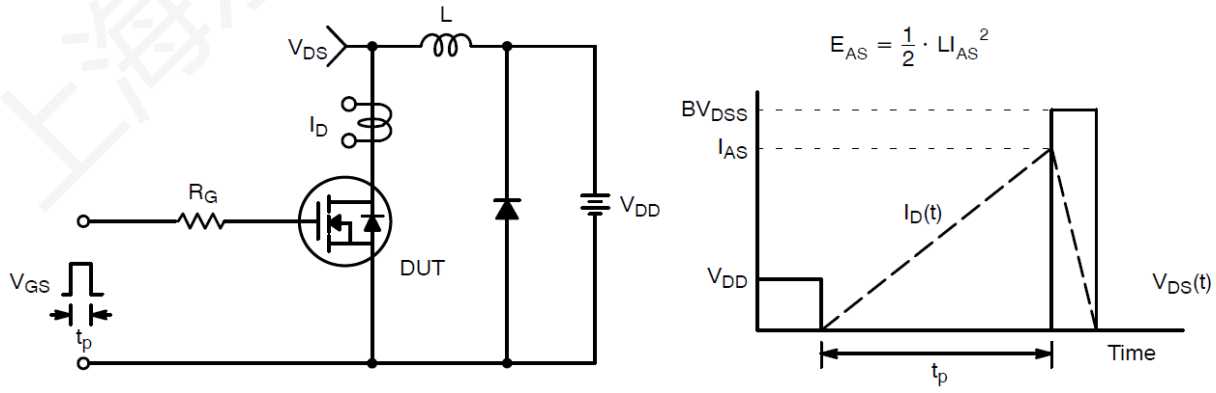


Figure 16: Unclamped Inductive Switching Test Circuit & Waveforms

P-Channel Electrical Characteristic (T_J = 25 °C, unless otherwise specified):

Static Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
V_{DSS}	Drain to Source Breakdown Voltage	V_{GS}=0V, I_D=-250μA	-30	--	--	V
I_{DSS}	Drain to Source Leakage Current	V_{DS}=-30V, V_{GS}=0V	--	--	-1.0	μA
$I_{GSS(F)}$	Gate to Source Forward Leakage	V_{GS}=-20V, V_{DS}=0V	--	--	-100	nA
$I_{GSS(R)}$	Gate to Source Reverse Leakage	V_{GS}=+20V, V_{DS}=0V	--	--	100	nA
$V_{GS(TH)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=-250μA	-1.0	-1.5	-2.0	V
$R_{DS(ON)1}$	Drain-to-Source On-Resistance	V_{GS}=-10V, I_D=-10A	--	20.5	25	mΩ
$R_{DS(ON)2}$	Drain-to-Source On-Resistance	V_{GS}=-4.5V, I_D=-8.0A	--	29	39	mΩ

Dynamic Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
C_{iss}	Input Capacitance	V_{GS} =0V V_{DS} =-15V f =1.0MHz	--	723	--	pF
C_{oss}	Output Capacitance		--	109	--	
C_{rss}	Reverse Transfer Capacitance		--	97	--	
R_G	Gate resistance	V_{GS}=0V,V_{DS}=0V,f=1MHz	--	11	--	Ω

Resistive Switching Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
$t_{d(ON)}$	Turn-on Delay Time	I_D =-10A V_{DS} =-15V V_{GS} =-10V R_G =3.0Ω	--	20	--	ns
t_r	Rise Time		--	30	--	
$t_{d(OFF)}$	Turn-Off Delay Time		--	45	--	
t_f	Fall Time		--	15	--	
Q_g	Total Gate Charge	V_{GS} =-10V V_{DS} =-15V I_D =-10A	--	17	--	nC
Q_{gs}	Gate to Source Charge		--	2.5	--	
Q_{gd}	Gate to Drain Charge		--	3.2	--	

Source-Drain Diode Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
I_S	Diode Forward Current	T_C=25 °C	--	--	-20	A
V_{SD}	Diode Forward Voltage	I_S=-10A, V_{GS}=0V	--	--	-1.2	V

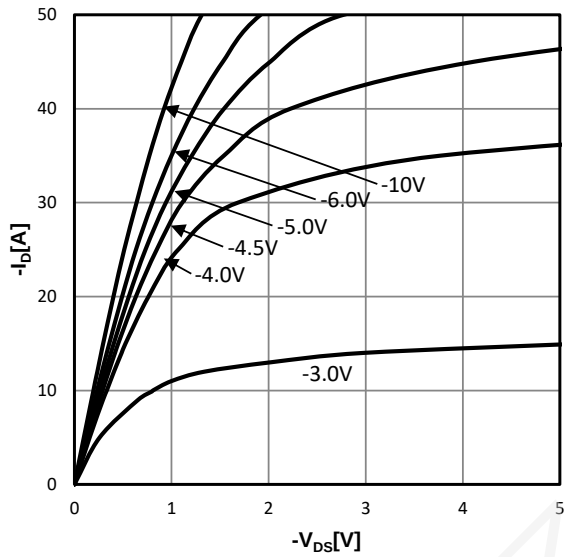
a1：Repetitive rating; pulse width limited by maximum junction temperature

a2：V_{DD}=-15V,L=0.1mH, R_G=25Ω, Starting T_j=25℃

a3：Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm^2 (one layer, 70 μm thick) copper area for drain connection.

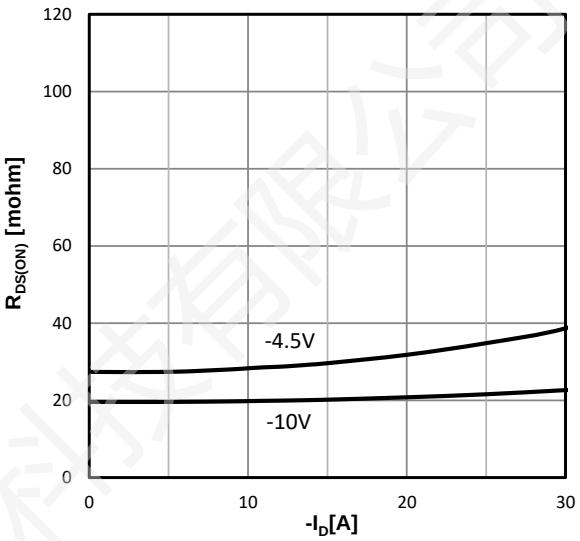
P-Channel Characteristics Curve：

Figure 1: Typ. output characteristics



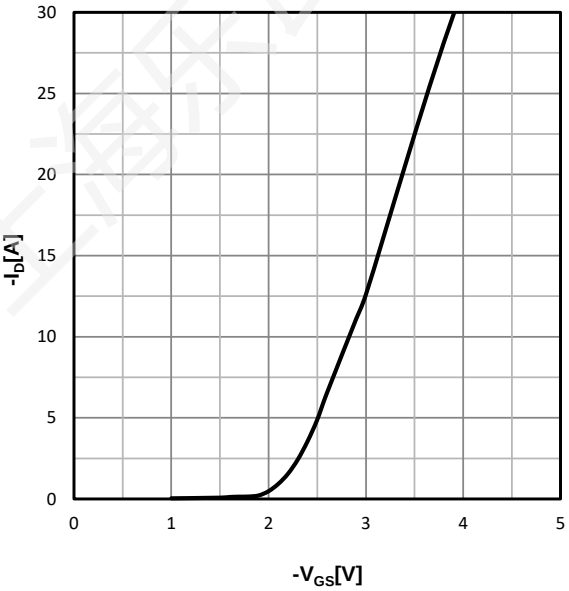
$I_D=f(V_{DS})$, T_j=25 °C; parameter: V_{GS}

Figure 2: Typ. drain-source on resistance



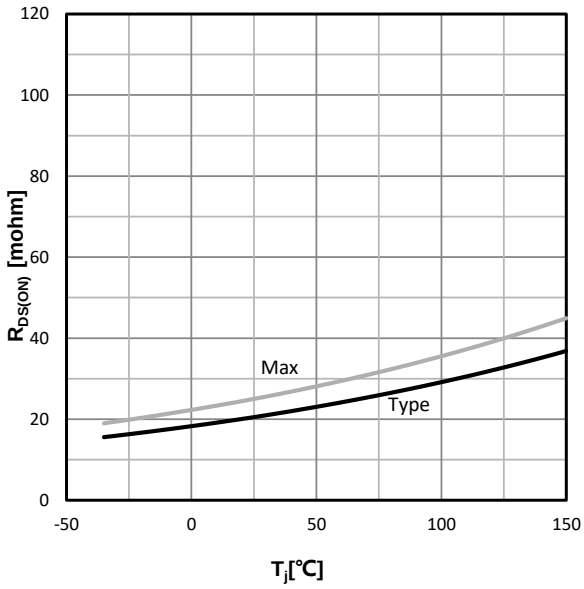
$R_{DS(on)}=f(I_D)$, T_j=25 °C; parameter: V_{GS}

Figure 3: Typ. transfer characteristics



$I_D=f(V_{GS})$, $|V_{DS}|>2|I_D|R_{DS}(on)max$;

Figure 4: drain-source on resistance



$R_{DS(on)}=f(T_j)$, I_D=-10A, V_{GS}=-10V;

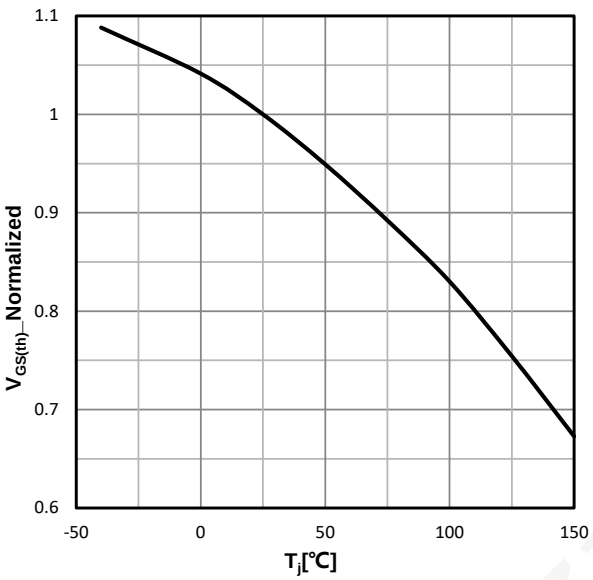
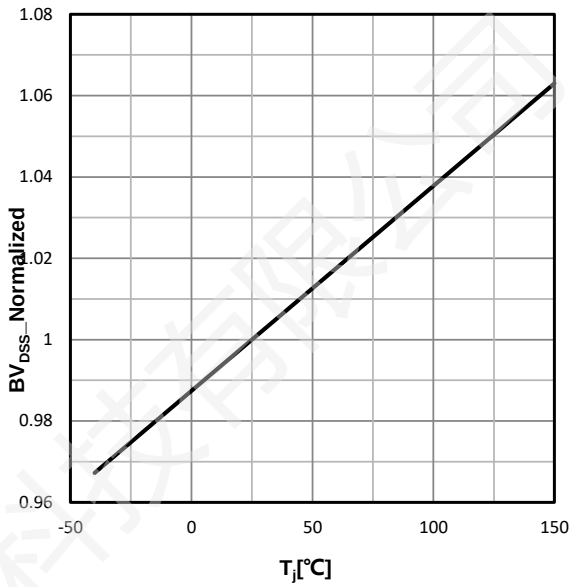
Figure 5: Typ. gate threshold voltage	Figure 6: Drain-source breakdown voltage
	
$V_{GS}=f(T_j)$,$V_{GS}=V_{DS,}$ I_D=-250μA;	$V_{BR(DSS)}=f(T_j)$; I_D=-250μA;

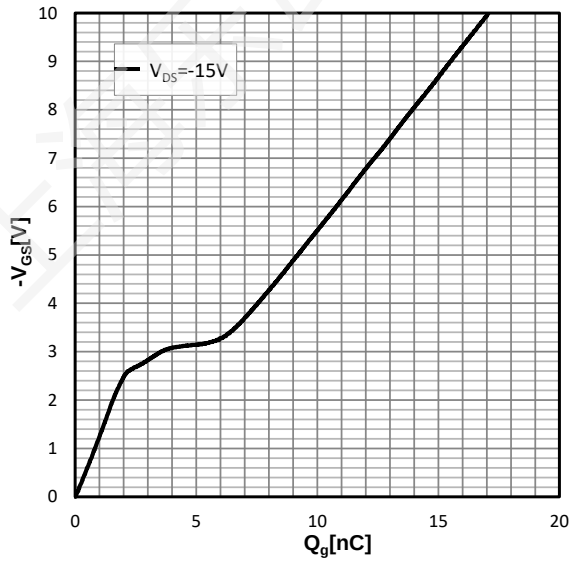
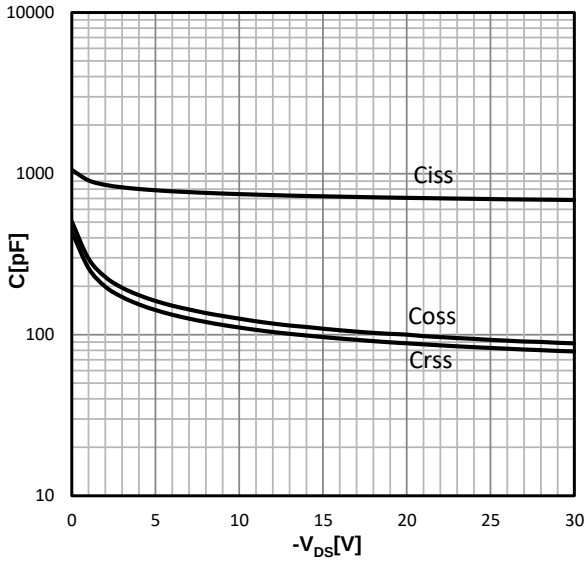
Figure 7: Typ. gate charge	Figure 8: Typ. Capacitances
	
$V_{GS}=f(Q_g)$, I_D=-10A, T_j=25 °C; parameter: V_{DS}	C=f(V_{DS}); V_{GS}=0V; f=1.0 MHz;

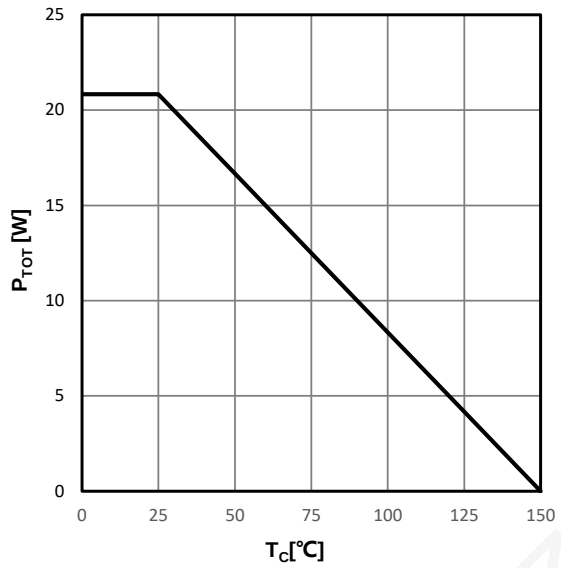
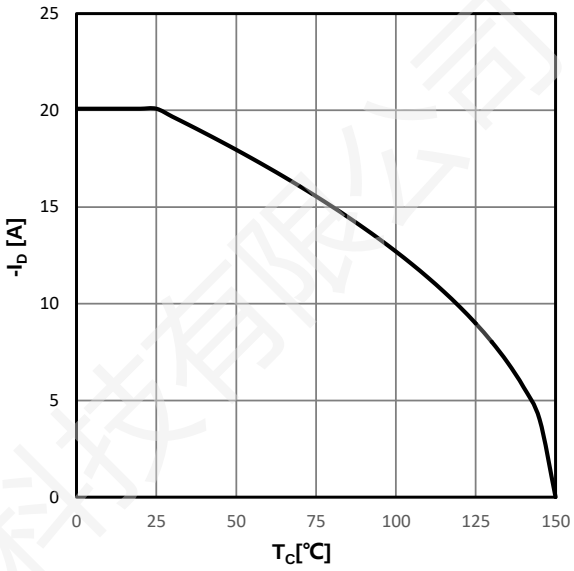
Figure 9: Power dissipation	Figure 10:Drain current
	
$P_{tot}=f(T_C)$;	$I_D=f(T_C)$;

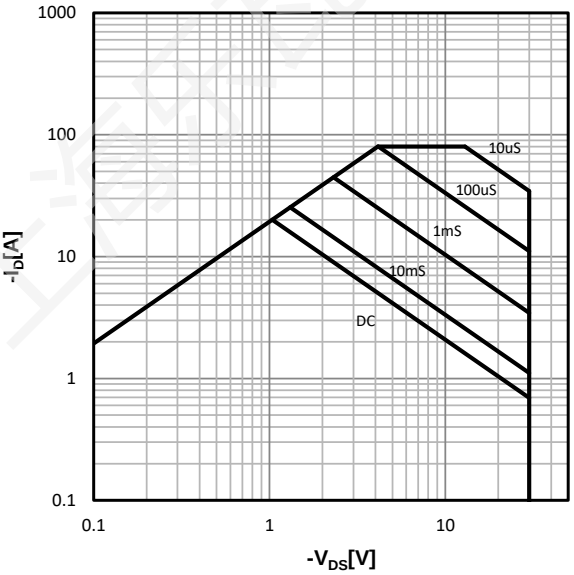
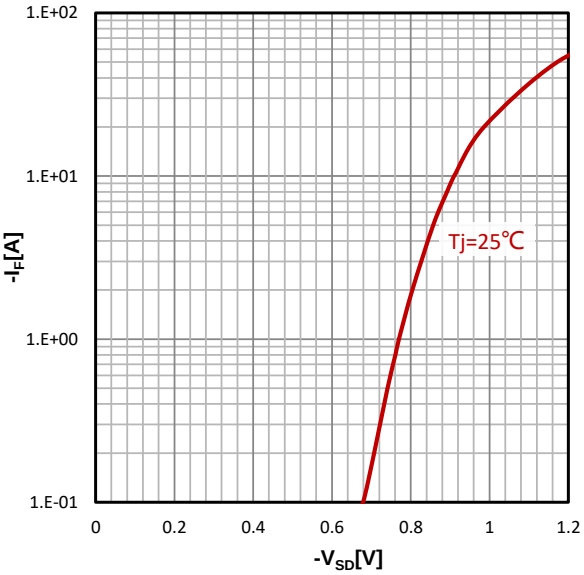
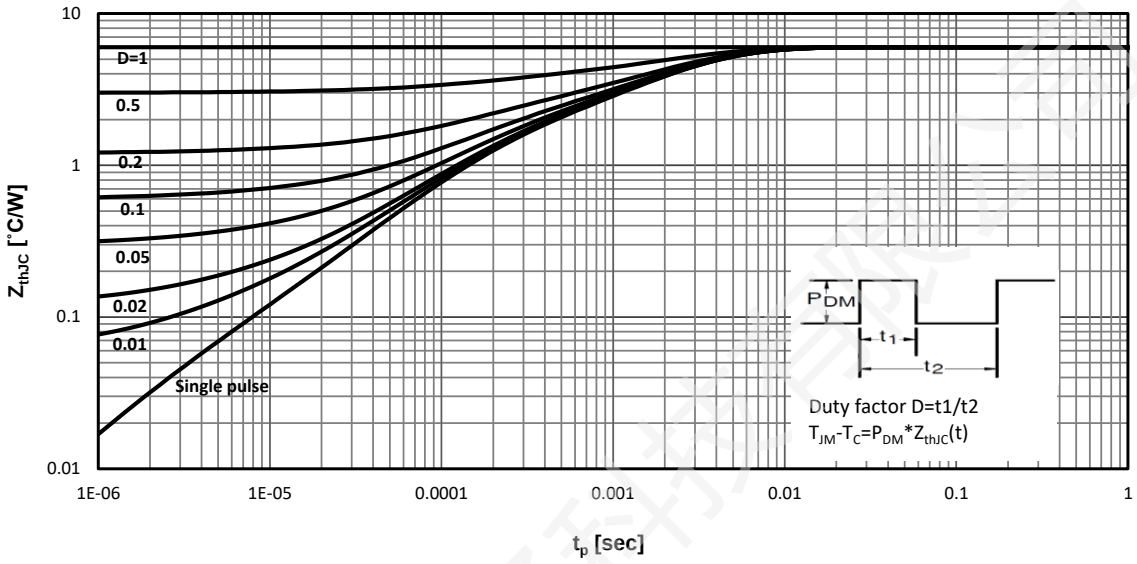
Figure 11: Safe operating area	Figure 12: Typ. forward characteristics
	
$I_D=f(V_{DS})$; T_C=25 °C; D=0; parameter: tp	$I_F=f(V_{SD})$;

Figure 13: Max. Transient Thermal Impedance



$Z_{thJC}=f(t_p)$; parameter: D

P-Channel Test Circuit & Waveform:

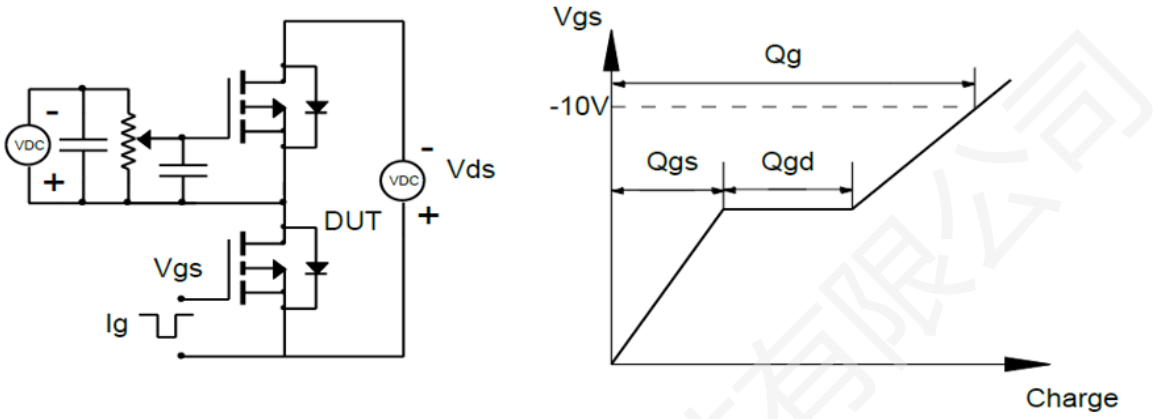


Figure 14: Gate Charge Test Circuit & Waveform

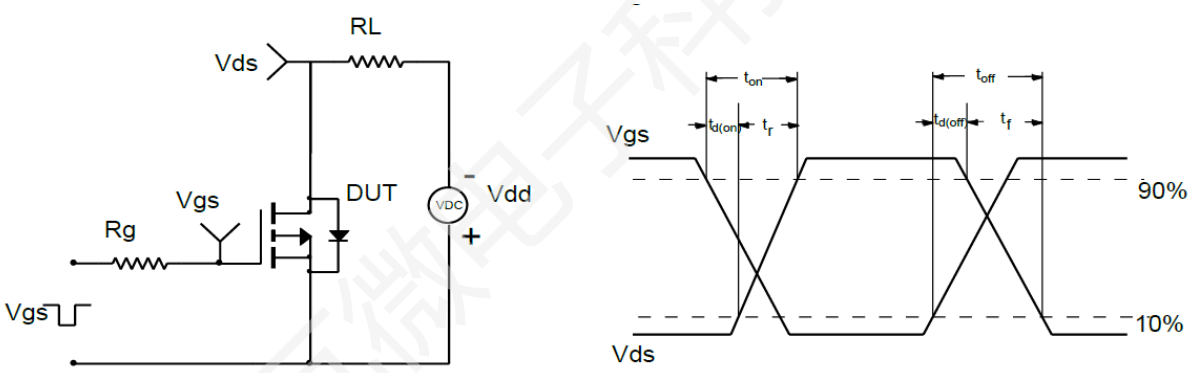


Figure 15: Resistive Switching Test Circuit & Waveforms

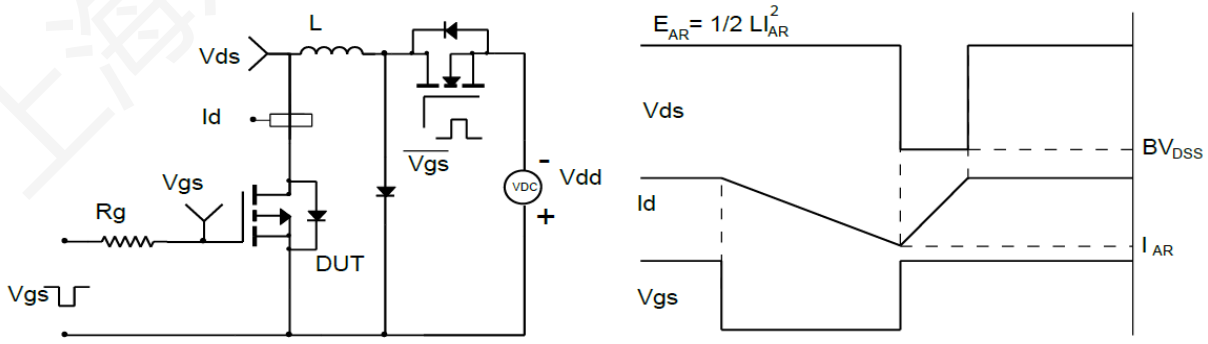
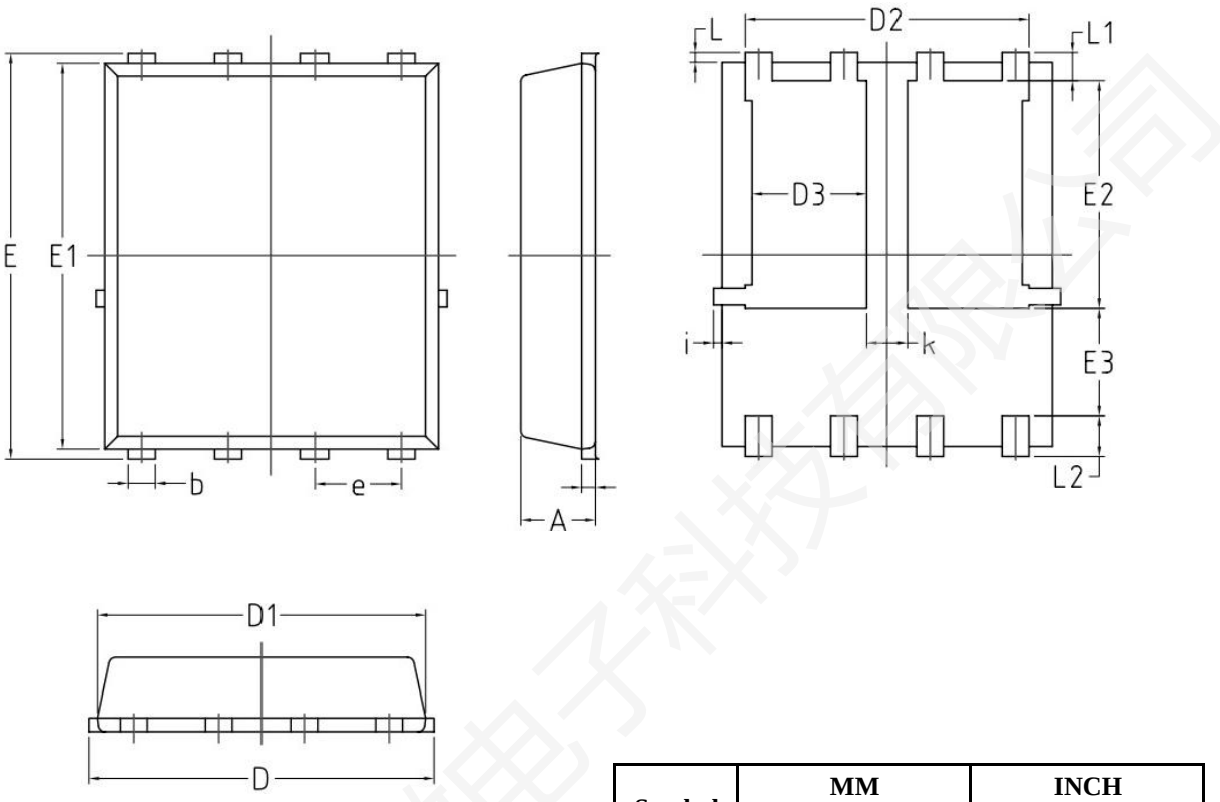


Figure 16: Unclamped Inductive Switching Test Circuit & Waveforms

Package Outline:



Symbol	MM		INCH	
	MIN	MAX	MIN	MAX
A	0.90	1.20	0.0354	0.0472
b	0.34	0.48	0.0134	0.0189
C	0.203 BSC		0.0080 BSC	
D	4.80	5.40	0.1890	0.2126
D1	4.80	5.00	0.1890	0.1969
D2	4.11	4.31	0.1620	0.1700
D3	1.60	1.80	0.0629	0.0708
E	5.90	6.15	0.2323	0.2421
E1	5.65	5.85	0.2224	0.2303
E2	3.30	3.60	0.1300	0.1417
E3	1.40	/	0.0551	/
e	1.27 BSC		0.05 BSC	
L	0.05	0.28	0.0019	0.0110
L1	0.38	0.58	0.0150	0.0228
L2	0.38	0.71	0.0150	0.0280
l	/	0.18	/	0.0070
k	0.50	0.70	0.0197	0.0276

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Revision History:

Revison	Date	Descriptions
Rev 1.2	Oct.2026	“P-Channel Electrical Characteristic” Update
Rev 1.1	Jun.2025	Initial Version

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